TRANSISTOR(PNP)

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

- **Low noise : NF= 1dB(Typ.),10dB (Max.)**
- **Complementary to 2SC2712.**
- **Small Package.**

MARKING: SO , SY , SG

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Current -Continuous	-150	mA
P_D	Collector Power Dissipation	150	mW
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55-125	℃

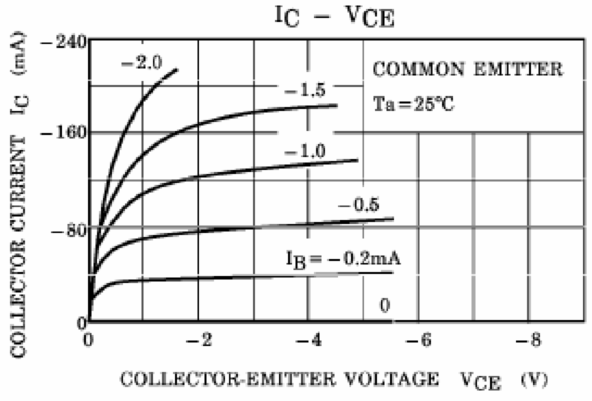
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

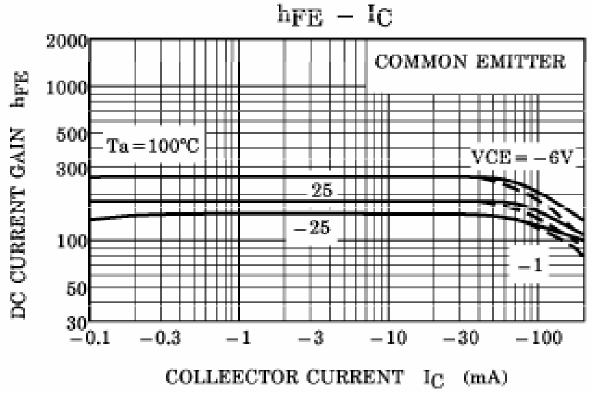
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100u A,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100 u A,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-0.1	u A
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	u A
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-2mA	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.3	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-1mA	80			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			7	pF
Noise figure	NF	V_{CE}=-6V,I_c=0.1mA, f=1KHZ,Rg=10KΩ			10	dB

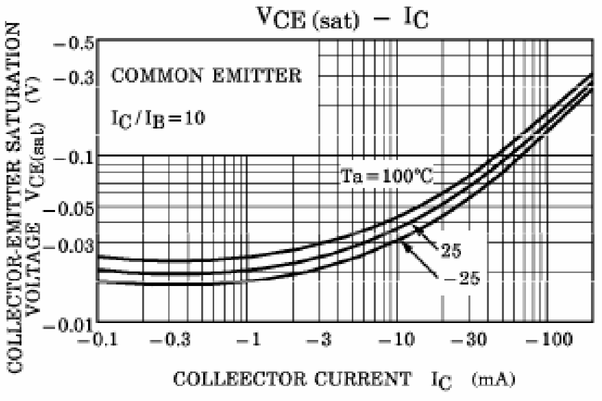
CLASSIFICATION OF h_{FE}

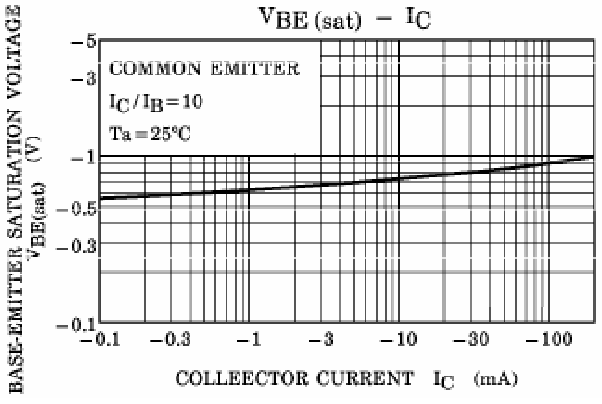
Rank	O	Y	GR(G)
Range	70-140	120-240	200-400

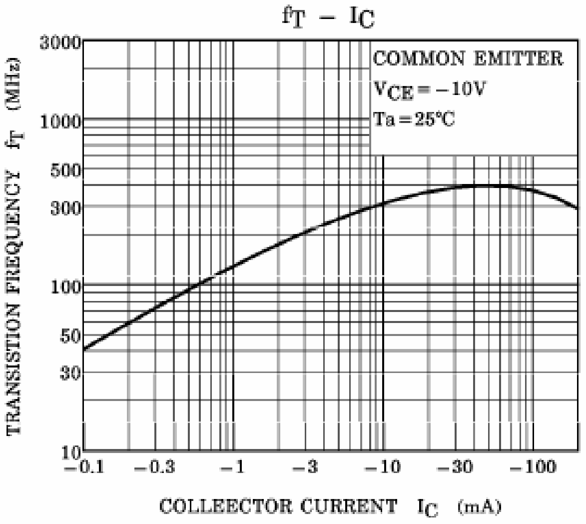
ypical Characteristics

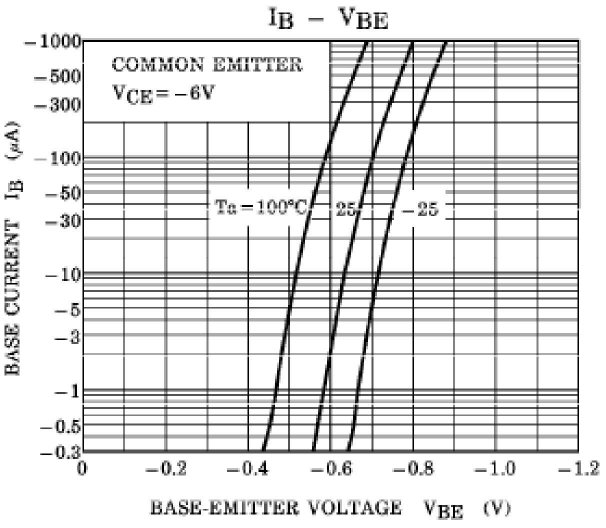

I_C – V_{CE}

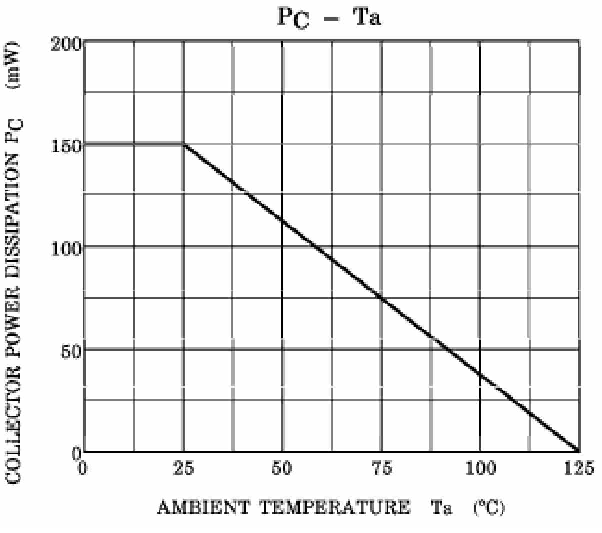

h_{FE} – I_C


V_{CE} (sat) – I_C


V_{BE} (sat) – I_C


f_T – I_C


I_B – V_{BE}


P_C – Ta